

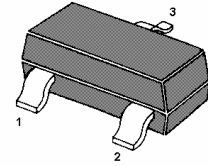
PBSS4240

40V; 2A NPN Low $V_{CE(sat)}$ (BISS) Transistor

SOT-23

FEATURES

- Low collector-emitter saturation voltage
- High current capability
- Improved device reliability due to reduced heat generation.



1.BASE 2.EMITTER 3.COLLECTOR

APPLICATIONS

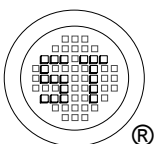
- Supply line switching circuits
- Battery management applications
- DC/DC converter applications
- Strobe flash units
- Heavy duty battery powered equipment (motor and lamp drivers).

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	40	V
Collector Emitter Voltage	V_{CEO}	40	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current (DC)	I_C	2	A
Peak Collector Current	I_{CM}	3	A
Peak Base Current	I_{BM}	300	mA
Total Power Dissipation	P_{tot}	$T_{amb} \leq 25^\circ\text{C}^1$	200
		$T_{amb} \leq 25^\circ\text{C}^2$	480
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_S	-65 to +150	$^\circ\text{C}$
Thermal Resistance From Junction to Ambient	$R_{th\ j-a}$	In free air ¹⁾	417
		In free air ²⁾	260
Operating Ambient Temperature	T_{amb}	-65 to +150	$^\circ\text{C}$

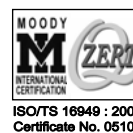
¹⁾ Device mounted on a printed-circuit board; single sided copper; tinplated and standard footprint.

²⁾ Device mounted on a printed-circuit board; single sided copper; tinplated; mounting pad for collector 1cm².



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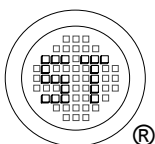


Dated : 20/10/2005

PBSS4240

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $V_{CE}=2\text{V}$, $I_C=100\text{mA}$	h_{FE}	350	-	-	
at $V_{CE}=2\text{V}$, $I_C=500\text{mA}$	h_{FE}	300	-	-	-
at $V_{CE}=2\text{V}$, $I_C=1\text{A}$	h_{FE}	250	-	-	
at $V_{CE}=2\text{V}$, $I_C=2\text{A}$	h_{FE}	80	-	-	
Collector-Base Cutoff Current					
at $V_{CB}=30\text{V}$	I_{CBO}	-	-	100	nA
at $V_{CB}=30\text{V}$, $T_{amb}=150\text{ }^{\circ}\text{C}$		-	-	50	μA
Emitter-Base Cutoff Current					
at $V_{EB}=4\text{V}$	I_{EBO}	-	-	100	nA
Collector-Emitter Saturation Voltage					
at $I_C=100\text{mA}$, $I_B=1\text{mA}$	$V_{CE(sat)}$	-	-	70	mV
at $I_C=500\text{mA}$, $I_B=50\text{mA}$		-	-	100	
at $I_C=750\text{mA}$, $I_B=15\text{mA}$		-	-	180	
at $I_C=1\text{A}$, $I_B=50\text{mA}$		-	-	180	
at $I_C=2\text{A}$, $I_B=200\text{mA}$		-	-	320	
Equivalent on-Resistance					
at $I_C=500\text{mA}$, $I_B=50\text{mA}$	$R_{CE(sat)}$	-	140	<200	m Ω
Base-Emitter Saturation Voltage					
at $I_C=2\text{A}$, $I_B=200\text{mA}$	$V_{BE(sat)}$	-	-	1.1	V
Base-Emitter Turn-on Voltage					
at $V_{CE}=2\text{V}$, $I_C=100\text{mA}$	$V_{BE(on)}$	-	-	0.75	V
Transition Frequency					
at $V_{CE}=10\text{V}$, $I_C=100\text{mA}$, $f=100\text{MHz}$	f_T	100	230	-	MHz
Collector Capacitance					
at $V_{CB}=10\text{V}$, $f=1\text{MHz}$	C_C	-	15	20	pF



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ISO/TS 16949 : 2002
Certificate No. 05103



ISO 14001:2004
Certificate No. 7116



ISO 9001:2000
Certificate No. 0506098

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